

Patent Abstracts of Japan

PUBLICATION NUMBER : 05182490
PUBLICATION DATE : 23-07-93

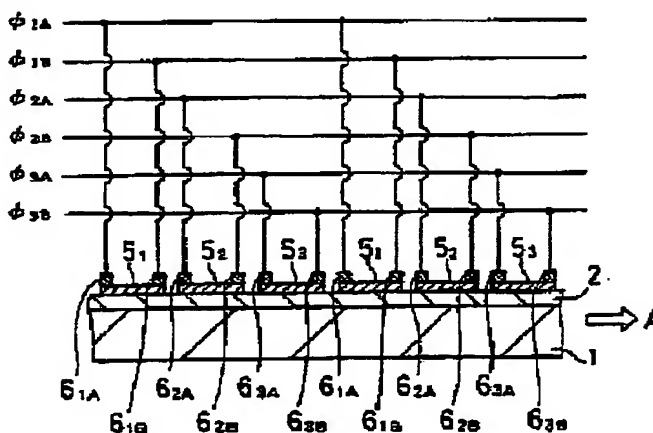
APPLICATION DATE : 01-04-92
APPLICATION NUMBER : 04109315

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INT.CL. : G11C 27/04 H01L 27/148 H04N 5/335

TITLE : CHARGE COUPLED DEVICE AND
METHOD FOR DRIVING IT



ABSTRACT : PURPOSE: To shorten a transfer time and to improve transfer efficiency.

CONSTITUTION: Transfer gate electrodes 5₁, 5₂, 5₃ consisting of high resistance polysilicon are arranged in a line repeatedly through an SiO₂ layer 2 on a substrate 1, and the transfer gate electrodes are provided with metal electrodes 6₁A, 6₂A, 6₃A on respective end parts of the opposite side to a charge transfer direction and provided with metal electrodes 6₁B, 6₂B, 6₃B on the end part of the charge transfer direction. Transfer clock pulses ϕ_{1A} , ϕ_{2A} , ϕ_{3A} (maximum V_2 , minimum V_1 of voltage value) are supplied to the metal electrodes 6₁A, 6₂A, 6₃A and the transfer clock pulses ϕ_{1B} , ϕ_{2B} , ϕ_{3B} (maximum $V_3(>V_2)$, minimum V_1 of voltage value) are supplied to the metal electrodes 6₁B, 6₂B, 6₃B. Electric field is generated under the transfer gate electrodes whose intensity enlarges in creasingly from the opposite direction side to the charge transfer direction facing to the charge transfer direction side and a potential well is formed on the boundary of Si-SiO₂ under the transfer gate electrode whose depth increases from the opposite direction side to the charge transfer direction facing to the charge transfer direction side.

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FP04-0100-00EP -HP
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SEARCH REPORT